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**Obert R. Wood II
Eric M. Panning**
Editors

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The CID Number appears on each page of the manuscript. The complete citation is used on the first page, and an abbreviated version on subsequent pages. Numbers in the index correspond to the last two digits of the six-digit CID Number.

Contents

Part One

- xv *Conference Committee*
xix *Introduction*

NEW EUV RESIST MATERIALS: JOINT SESSION WITH CONFERENCES 9048 AND 9051

- 9048 04 **EUV resists towards 11nm half-pitch** [9048-3]
Y. Ekinçi, M. Vockenhuber, N. Mojarad, D. Fan, Paul Scherrer Institut (Switzerland)
- 9048 05 **Investigation of novel inorganic resist materials for EUV lithography** [9048-4]
M. E. Krysak, J. M. Blackwell, S. E. Putna, M. J. Leeson, T. R. Younkin, S. Harlson, K. Frasure, F. Gstrein, Intel Corp. (United States)

STOCHASTICS AND EUV PROCESS IMPROVEMENTS: JOINT SESSION WITH CONFERENCES 9048 AND 9051

- 9048 06 **Stochastic effects in fabrication of 11nm line-and-space patterns using extreme ultraviolet lithography** [9048-5]
T. Kozawa, Osaka Univ. (Japan); J. J. Santillan, T. Itani, EUVL Infrastructure Development Ctr., Inc. (Japan)
- 9048 07 **Understanding EUV resist mottling leading to better resolution and linewidth roughness** [9048-6]
J. Thackeray, J. Cameron, V. Jain, P. LaBeaume, S. Coley, O. Ongayi, M. Wagner, Dow Electronic Materials (United States); J. Biafore, KLA-Tencor (United States); J. S. Chun, SEMATECH Inc. (United States) and SUNY College of Nanoscale Science and Engineering (United States)
- 9048 08 **Comparison of EUV patterning performance between PTD and NTD for 1Xnm DRAM** [9048-7]
C. Oh, H. Seo, E. Park, J. Lee, C. Bok, W. Kwon, S. Park, SK Hynix, Inc. (Korea, Republic of)
- 9048 09 **Impact of stochastic effects on EUV printability limits** [9048-8]
P. De Bisschop, J. Van de Kerkhove, J. Mailfert, IMEC (Belgium); A. Vaglio Pret, KLA-Tencor (Belgium) and IMEC (Belgium); J. Biafore, KLA-Tencor (United States)
- 9048 0A **EUV stochastic noise analysis and LCDU mitigation by etching on dense contact-hole array patterns** [9048-9]
S.-M. Kim, S. Koo, J.-T. Park, C.-M. Lim, M. Kim, SK Hynix, Inc. (Korea, Republic of); C.-N. Ahn, ASML Korea (Korea, Republic of); A. Fumar-Pici, ASML USA (United States); A. C. Chen, ASML Taiwan (Taiwan)

EUV SOURCE

- 9048 0C **LPP EUV source readiness for NXE 3300B** [9048-11]
D. C. Brandt, I. V. Fomenkov, N. R. Farrar, B. La Fontaine, D. W. Myers, D. J. Brown, A. I. Ershov, N. R. Böwering, D. J. Riggs, R. J. Rafac, S. De Dea, Cymer LLC (United States); R. Peeters, H. Meiling, N. Harned, D. Smith, A. Pirati, R. Kazinczi, ASML Netherlands B.V. (Netherlands)
- 9048 0D **Sub-hundred Watt operation demonstration of HVM LPP-EUV source** [9048-12]
H. Mizoguchi, H. Nakarai, T. Abe, T. Ohta, K. M. Nowak, Y. Kawasuji, H. Tanaka, Y. Watanabe, T. Hori, T. Kodama, Y. Shiraishi, T. Yanagida, T. Yamada, T. Yamazaki, S. Okazaki, T. Saitou, Gigaphoton Inc. (Japan)
- 9048 0E **Highly-efficient high-power pulsed CO₂ laser characterized by transverse-flow laser amplifiers** [9048-13]
Y. Tanino, J. Nishimae, T. Yamamoto, T. Tamida, K. Funaoka, S. Fujikawa, Mitsubishi Electric Corp. (Japan)
- 9048 0G **Spectral purity enhancement for the EUV lithography systems by suppressing UV reflection from multilayers** [9048-15]
Q. Huang, FOM Institute DIFFER (Netherlands) and Univ. of Twente (Netherlands); M. de Boer, J. Barreux, Univ. of Twente (Netherlands); D. M. Paardekooper, Univ. of Leiden (Netherlands); T. van den Boogaard, FOM Institute DIFFER (Netherlands); R. van de Kruijs, FOM Institute DIFFER (Netherlands) and Univ. of Twente (Netherlands); E. Zoethout, FOM Institute DIFFER (Netherlands); E. Louis, F. Bijkerk, FOM Institute DIFFER (Netherlands) and Univ. of Twente (Netherlands)

EUV MASK I

- 9048 0H **Production of EUV mask blanks with low killer defects** [9048-16]
A. O. Antohe, P. Kearney, M. Godwin, L. He, A. JohnKadaksham, F. Goodwin, SEMATECH Inc. (United States); A. Weaver, A. Hayes, S. Trigg, Veeco Instruments Inc. (United States)
- 9048 0I **Mitigation of EUV mask blank substrate pit and scratch defects by Accelerated Neutral Atom Beam (ANAB) processing** [9048-17]
M. Walsh, K. Chau, S. Kirkpatrick, R. Svrluga, B. Piwczyk, Exogenesis Corp. (United States); F. Goodwin, D. Balachandran, SEMATECH Inc. (United States)
- 9048 0J **Durability of Ru-based EUV masks and the improvement** [9048-18]
S. Lee, J. Kim, S.-W. Koh, I. Jang, J. Choi, H. Ko, H.-S. Seo, S.-S. Kim, B. G. Kim, C.-U. Jeon, SAMSUNG Electronics Co., Ltd. (Korea, Republic of)

EUV MASK II

- 9048 0L **Study of alternative capping and absorber layers for extreme ultraviolet (EUV) masks for sub-16nm half-pitch nodes** [9048-20]
A. Rastegar, M. House, R. Tian, SEMATECH Inc. (United States); T. Laursen, SUNY College of Nanoscale Science and Engineering (United States); A. Antohe, P. Kearney, SEMATECH Inc. (United States)

- 9048 OM **Evaluation of mask repair strategies via focused electron, helium, and neon beam induced processing for EUV applications** [9048-21]
C. M. Gonzalez, The Univ. of Tennessee Knoxville (United States); W. Slingenbergh, Univ. of Groningen (Netherlands); R. Timilsina, J.-H. Noh, M. G. Stanford, B. B. Lewis, The Univ. of Tennessee Knoxville (United States); K. L. Klein, Univ. of District of Columbia (United States); T. Liang, Intel Corp. (United States); J. D. Fowlkes, Oak Ridge National Lab. (United States); P. D. Rack, The Univ. of Tennessee Knoxville (United States) and Oak Ridge National Lab. (United States)
- 9048 ON **Effect of cleaning and storage on quartz substrate adhesion and surface energy** [9048-22]
D. Balachandran, A. John, SEMATECH Inc. (United States)
- 9048 OO **Direct measurement of carbon contamination topography on patterned EUV masks** [9048-23]
Y.-J. Fan, SEMATECH Inc. (United States); T. Murray, SUNY College of Nanoscale Science and Engineering (United States); F. Goodwin, D. Ashworth, SEMATECH Inc. (United States); G. Denbeaux, SUNY College of Nanoscale Science and Engineering (United States)
- 9048 OP **Particle control challenges in process chemicals and ultra-pure water for sub-10nm technology nodes** [9048-24]
A. Rastegar, M. Samayoa, M. House, H. Kurtuldu, S.-K. Eah, L. Morse, J. Harris-Jones, SEMATECH Inc. (United States)

EUV INTEGRATION

- 9048 OQ **EUV source-mask optimization for 7nm node and beyond** [9048-25]
X. Liu, R. Howell, S. Hsu, K. Yang, K. Gronlund, F. Driessen, H.-Y. Liu, ASML Brion (United States); S. Hansen, ASML Technology Development Ctr. (United States); K. van Ingen Schenau, T. Hollink, P. van Adrichem, K. Troost, ASML Netherlands B.V. (Netherlands); J. Zimmermann, O. Schumann, C. Hennerkes, P. Gräupner, Carl Zeiss SMT GmbH (Germany)
- 9048 OR **EUV overlay strategy for improving MMO** [9048-26]
B. Lee, I. Lee, Y. Hyun, S. Kim, C.-M. Lim, M. S. Kim, S. Park, SK Hynix Semiconductor Inc. (Korea, Republic of)
- 9048 OS **Prospects of DUV OoB suppression techniques in EUV lithography** [9048-27]
C.-M. Park, I. Kim, S.-H. Kim, D.-W. Kim, M.-S. Hwang, S.-N. Kang, C. Park, H.-W. Kim, J.-H. Yeo, S.-S. Kim, SAMSUNG Electronics Co., Ltd. (Korea, Republic of)
- 9048 OT **Feasibility of compensating for EUV field edge effects through OPC** [9048-28]
C. Maloney, Rochester Institute of Technology (United States), Mentor Graphics Corp. (United States), and IMEC (Belgium); J. Word, Mentor Graphics Corp. (United States); G. L. Fenger, Mentor Graphics Corp. (United States) and IMEC (Belgium); A. Niroomand, Micron Technology, Inc. (United States) and IMEC (Belgium); G. F. Lorusso, R. Jonckheere, E. Hendrickx, IMEC (Belgium); B. W. Smith, Rochester Institute of Technology (United States)
- 9048 OU **Comprehensive defect avoidance framework for mitigating EUV mask defects** [9048-29]
A. A. Kagalwalla, P. Gupta, Univ. of California, Los Angeles (United States)

- 9048 0V **Pattern fidelity verification for logic design in EUV lithography** [9048-30]
M. Sugawara, Sony Corp. (Belgium); E. Hendrickx, V. Philipsen, IMEC (Belgium); C. Maloney, G. Fenger, Mentor Graphics Corp. (United States)
- 9048 0W **EUV OPC modeling and correction requirements** [9048-31]
T. H. Coskun, T. Wallow, GLOBALFOUNDRIES Inc. (United States); G. S. Chua, GLOBALFOUNDRIES Singapore (Singapore); K. Standiford, C. Higgins, Y. Zou, GLOBALFOUNDRIES Inc. (United States)

EUV MASK METROLOGY

- 9048 0X **Actinic review of EUV masks: first results from the AIMS EUV system integration (Invited Paper)** [9048-32]
M. R. Weiss, D. Hellweg, Carl Zeiss SMT GmbH (Germany); J. H. Peters, S. Perlitz, A. Garetto, Carl Zeiss SMS GmbH (Germany); M. Goldstein, SEMATECH Inc. (United States);
- 9048 0Y **Actinic mask imaging: recent results and future directions from the SHARP EUV microscope** [9048-33]
K. A. Goldberg, M. P. Benk, A. Wojdyla, I. Mochi, S. B. Rekawa, A. P. Allezy, M. R. Dickinson, C. W. Cork, W. Chao, D. J. Zehm, J. B. Macdougall, P. P. Naulleau, Lawrence Berkeley National Lab. (United States); A. Rudack, SEMATECH Inc. (United States)
- 9048 0Z **EUV patterned mask inspection with an advanced projection electron microscope (PEM) system** [9048-34]
R. Hirano, S. Iida, T. Amano, T. Terasawa, H. Watanabe, EUVL Infrastructure Development Ctr., Inc. (Japan); M. Hatakeyama, T. Murakami, K. Terao, EBARA Corp. (Japan)
- 9048 10 **Zernike phase contrast microscope for EUV mask inspection** [9048-35]
Y.-G. Wang, Lawrence Berkeley National Lab. (United States) and Univ. of California, Berkeley (United States); R. Miyakawa, Lawrence Berkeley National Lab. (United States); A. Neureuther, Lawrence Berkeley National Lab. (United States) and Univ. of California, Berkeley (United States); P. Naulleau, Lawrence Berkeley National Lab. (United States)
- 9048 11 **A novel concept for actinic EUV mask review tool using a scanning lensless imaging method at the Swiss Light Source** [9048-36]
S. Lee, M. Guizar-Sicairos, Y. Ekinici, Paul Scherrer Institut (Switzerland)
- 9048 12 **E-beam inspection of EUV mask defects: To etch or not to etch?** [9048-37]
R. Bonam, IBM Research Div. (United States); H.-Y. Tien, Hermes Microvision (United States); C. Park, GLOBALFOUNDRIES Inc (United States); S. Halle, IBM Research Div. (United States); F. Wang, Hermes Microvision (United States); D. Corliss, IBM Research Div. (United States); W. Fang, J. Jau, Hermes Microvision (United States)

METROLOGY SOURCES AND MODELING

- 9048 13 **High-radiance LDP source for mask inspection application** [9048-38]
Y. Teramoto, B. Santos, G. Mertens, R. Kops, M. Kops, Ushio Inc. (Germany); F. Küpper, Fraunhofer-Institut für Lasertechnik (Germany); G. Niimi, H. Yabuta, A. Nagano, T. Yokoyama, M. Yoshioka, T. Shirai, N. Ashizawa, H. Sato, K. Nakamura, K. Kasama, Ushio Inc. (Japan)
- 9048 16 **Enhancing the performance of LPP sources for EUV and BEUV lithography** [9048-41]
T. Szyuk, A. Hassanein, Purdue Univ. (United States)

EUV RESIST OUTGAS TESTING

- 9048 19 **Contribution of EUV resist components to the non-cleanable contaminations** [9048-44]
E. Shiobara, T. Takahashi, N. Sugie, Y. Kikuchi, I. Takagi, K. Katayama, H. Tanaka, S. Inoue, EUVL Infrastructure Development Ctr., Inc. (Japan); T. Watanabe, T. Harada, H. Kinoshita, Univ. of Hyogo (Japan)
- 9048 1A **Resist outgassing contamination on EUV multilayer mirror analogues** [9048-45]
D. Alvarado, Y. Kandel, SUNY College of Nanoscale Science and Engineering (United States); J. Sohn, T. Chakraborty, D. Ashworth, SEMATECH Inc. (United States); G. Denbeaux, SUNY College of Nanoscale Science and Engineering (United States)
- 9048 1B **Relationship between resist outgassing and EUV witness sample contamination in NXE outgas qualification using electrons and EUV photons** [9048-46]
I. Pollentier, A. Tirumala Venkata, R. Gronheid, IMEC (Belgium)

EUV RESIST I

- 9048 1C **Increasing sensitivity of oxide nanoparticle photoresists** [9048-47]
S. Chakrabarty, Cornell Univ. (United States); C. Sarma, SEMATECH Inc. (United States); L. Li, E. P. Giannelis, C. K. Ober, Cornell Univ. (United States)
- 9048 1D **Novel EUV resist materials for 16nm half pitch and EUV resist defects** [9048-48]
M. Shiratani, T. Naruoka, JSR Corp. (Japan); K. Maruyama, R. Ayothi, Y. Hishiro, JSR Micro, Inc. (United States); K. Hoshiko, A. Santos, X. Buch, JSR Micro N.V. (Belgium); T. Kimura, JSR Corp. (Japan)
- 9048 1E **Novel EUV resist materials design for 14nm half pitch and below** [9048-49]
H. Tsubaki, S. Tarutani, T. Fujimori, H. Takizawa, T. Goto, FUJIFILM Corp. (Japan)
- 9048 1F **Electron and hole transfer in anion-bound chemically amplified resists used in extreme ultraviolet lithography** [9048-50]
Y. Komuro, Osaka Univ. (Japan) and Tokyo Ohka Kogyo Co., Ltd. (Japan); H. Yamamoto, Osaka Univ. (Japan); Y. Utsumi, K. Ohmori, Tokyo Ohka Kogyo Co., Ltd. (Japan); T. Kozawa, Osaka Univ. (Japan)

- 9048 1H **Comparative analysis of shot noise in EUV and e-beam lithography** [9048-52]
S. Bhattarai, Univ. of California, Berkeley (United States) and Lawrence Berkeley National Lab. (United States); W. Chao, Lawrence Berkeley National Lab. (United States); A. R. Neureuther, Univ. of California, Berkeley (United States) and Lawrence Berkeley National Lab. (United States); P. P. Naulleau, Lawrence Berkeley National Lab. (United States)
- 9048 1I **Improved measurement capabilities at the NIST EUV reflectometry facility** [9048-53]
C. Tarrio, S. Grantham, T. A. Germer, J. Rife, T. B. Lucatorto, National Institute of Standards and Technology (United States); M. Kriese, Y. Platonov, L. Jiang, J. Rodríguez, Rigaku Innovative Technologies, Inc. (United States)

EXPOSURE TOOLS AND EXTENDIBILITY

- 9048 1J **EUV lithography: NXE platform performance overview (Invited Paper)** [9048-54]
R. Peeters, S. Lok, J. Mallman, M. van Noordenburg, N. Harned, ASML Netherlands B.V. (Netherlands); P. Kuerz, M. Lowisch, Carl Zeiss SMT AG (Germany); E. van Setten, G. Schiffelers, A. Pirati, J. Stoeldraijer, ASML Netherlands B.V. (Netherlands); D. Brandt, N. Farrar, I. Fomenkov, ASML Netherlands B.V. (United States); H. Boom, H. Meiling, R. Kool, ASML Netherlands B.V. (Netherlands)
- 9048 1K **Projection optics for EUVL micro-field exposure tools with 0.5 NA** [9048-55]
H. Glatzel, Zygo Corp. (United States); D. Ashworth, SEMATECH Inc. (United States); D. Bajuk, M. Bjork, M. Bremer, M. Cordier, Zygo Corp. (United States); K. Cummings, SEMATECH Inc. (United States); L. Girard, Zygo Corp. (United States); M. Goldstein, SEMATECH Inc. (United States); E. Gullikson, Lawrence Berkeley National Lab. (United States); S. Hardy, Zygo Corp. (United States); R. Hudyma, Hyperion Development LLC (United States); J. Kennon, R. Kestner, L. Marchetti, K. Nouri, Zygo Corp. (United States); P. Naulleau, Lawrence Berkeley National Lab. (United States); D. Pierce, Zygo Corp. (United States); R. Soufli, Lawrence Livermore National Lab. (United States); E. Spiller, Spiller X-ray Optics (United States); Y. Verma, Zygo Corp. (United States)
- 9048 1L **Across scanner platform optimization to enable EUV lithography at the 10-nm logic node** [9048-56]
J. Mulkens, J. Karssenbergh, H. Wei, M. Beckers, L. Verstappen, ASML Netherlands B.V. (Netherlands); S. Hsu, G. Chen, ASML Brion (United States)
- 9048 1M **Update on the SEMATECH 0.5 NA Extreme-Ultraviolet Lithography (EUVL) Microfield Exposure Tool (MET)** [9048-57]
K. Cummings, D. Ashworth, SEMATECH Inc. (United States); M. Bremer, R. Chin, Zygo Corp. (United States); Y.-J. Fan, SEMATECH Inc. (United States); L. Girard, H. Glatzel, Zygo Corp. (United States); M. Goldstein, SEMATECH Inc. (United States); E. Gullikson, Lawrence Berkeley National Lab. (United States); J. Kennon, B. Kestner, L. Marchetti, Zygo Corp. (United States); P. Naulleau, Lawrence Berkeley National Lab. (United States); R. Soufli, Lawrence Livermore National Lab. (United States); J. Bauer, M. Mengel, J. Welker, M. Grupp, E. Sohmen, Carl Zeiss SMT GmbH (Germany); S. Wurm, SEMATECH Inc. (United States)

- 9048 1N **Progress on EUV pellicle development** [9048-58]
C. Zoldesi, K. Bal, ASML Netherlands B.V. (Netherlands); B. Blum, ASML (United States); G. Bock, D. Brouns, F. Dhalluin, N. Dziomkina, J. D. A. Espinoza, J. de Hoogh, S. Houweling, M. Jansen, M. Kamali, A. Kempa, R. Kox, R. de Kruif, J. Lima, Y. Liu, H. Meijer, H. Meiling, I. van Mil, M. Reijnen, L. Scaccabarozzi, D. Smith, B. Verbrugge, L. de Winters, ASML Netherlands B.V. (Netherlands); X. Xiong, J. Zimmerman, ASML (United States)
- 9048 1O **Driving the industry towards a consensus on high numerical aperture (high-NA) extreme ultraviolet (EUV)** [9048-59]
P. A. Kearney, SEMATECH Inc. (United States); O. Wood, GLOBALFOUNDRIES Inc. (United States); E. Hendrickx, IMEC (Belgium); G. McIntyre, IBM Microelectronics (United States); S. Inoue, EUVL Infrastructure Development Ctr., Inc. (Japan); F. Goodwin, S. Wurm, SEMATECH Inc. (United States); J. van Schoot, ASML Netherlands B.V. (Netherlands); W. Kaiser, Carl Zeiss SMT GmbH (Germany)

Part Two

EUV MANUFACTURING

- 9048 1Q **Integration of an EUV metal layer: a 20/14nm demo (Invited Paper)** [9048-61]
C. Higgins, E. Verduijn, X. Hu, L. Wang, GLOBALFOUNDRIES Inc. (United States); M. Singh, Newport Corp. (Netherlands); J. Wandell, S. Mehta, J. R. Fakhoury, M. Zaleski, GLOBALFOUNDRIES Inc. (United States); Y. Zou, Brion Technologies (United States); H. P. Koh, P. Mangat, GLOBALFOUNDRIES Inc. (United States)
- 9048 1R **The economic impact of EUV lithography on critical process modules** [9048-62]
A. Mallik, N. Horiguchi, J. Bömmels, A. Thean, K. Barla, G. Vandenberghe, K. Ronse, J. Ryckaert, A. Mercha, L. Altimime, D. Verkest, A. Steegen, IMEC (Belgium)
- 9048 1S **High-resist sensitization by pattern and flood combination lithography** [9048-106]
S. Tagawa, A. Oshima, S. Enomoto, C. Q. Dinh, Osaka Univ. (Japan)

POSTER SESSION

- 9048 1T **EUV source modeling** [9048-63]
S. Kulkarni, I. Golovkin, J. MacFarlane, Prism Computational Sciences, Inc. (United States)
- 9048 1U **A study of the effect of pellicle support structures on aerial-image quality in EUV lithography by rigorous electromagnetic simulation** [9048-64]
M. S. Yeung, Fastlitho Inc. (United States); E. Barouch, Boston Univ. (United States); H.-K. Oh, Hanyang Univ. (Korea, Republic of)
- 9048 1V **Emission properties of tin droplets laser-produced-plasma light sources** [9048-66]
H. Chen, X. Wang, D. Zuo, P. Lu, H. Zhu, Huazhong Univ. of Science and Technology (China); T. Wu, Wuhan Institute of Technology (China)

- 9048 1W **Design and synthesis of novel resist materials for EUVL** [9048-67]
V. S. V. Satyanarayana, V. Singh, S. Ghosh, S. Sharma, Indian Institute of Technology Mandi (India); K. E. Gonsalves, Indian Institute of Technology Mandi (India) and The Univ. of North Carolina at Charlotte (United States)
- 9048 1X **Imaging performance of attenuated phase-shift mask using coherent scattering microscope** [9048-68]
J. U. Lee, S. Jeong, S. C. Hong, S. M. Lee, J. Ahn, Hanyang Univ. (Korea, Republic of)
- 9048 1Y **Optimization of processing parameters and metrology for novel NCA negative resists for NGL** [9048-69]
V. Singh, V. S. V. Satyanarayana, Indian Institute of Technology Mandi (India); F. Kessler, F. R. Scheffer, D. E. Weibel, Univ. Federal do Rio Grande do Sul (Brazil); S. K. Sharma, S. Ghosh, Indian Institute of Technology Mandi (India); K. E. Gonsalves, Indian Institute of Technology Mandi (India) and The Univ. of North Carolina at Charlotte (United States)
- 9048 1Z **SEMATECH's cycles of learning test for EUV photoresist and its applications for process improvement** [9048-70]
J. S. Chun, SEMATECH Inc. (United States) and SUNY College of Nanoscale Science and Engineering (United States); S.-H. Jen, K. Petrillo, C. Montgomery, D. Ashworth, M. Neisser, SEMATECH Inc. (United States); T. Saito, L. Huli, D. Hetzer, TEL Technology Ctr., America, LLC (United States)
- 9048 20 **Improvement of defect mitigation with EUV actinic blank inspection prototype for 16 nm hp** [9048-71]
T. Murachi, T. Amano, EUVL Infrastructure Development Ctr., Inc. (Japan); T. Suzuki, H. Miyai, Lasertec Corp. (Japan)
- 9048 22 **Experimental verification of the effect of phase defect shape on ABI signal intensity** [9048-73]
N. Takagi, T. Terasawa, Y. Arisawa, EUVL Infrastructure Development Ctr., Inc. (Japan)
- 9048 24 **Repetitive operation of counter-facing plasma focus device: toward a practical light source for EUV lithography** [9048-75]
T. Sodekoda, H. Kuwabara, IHI Corp. (Japan); M. Masuda, S. Liu, K. Kanou, K. Kawaguchi, K. Horioka, Tokyo Institute of Technology (Japan)
- 9048 25 **At wavelength observation of phase defect embedded in EUV mask using microscope technique** [9048-76]
T. Terasawa, T. Amano, T. Yamane, H. Watanabe, EUVL Infrastructure Development Ctr., Inc. (Japan); M. Toyoda, Tohoku Univ. (Japan); T. Harada, T. Watanabe, H. Kinoshita, Univ. of Hyogo (Japan)
- 9048 27 **Observation of phase defect on extreme ultraviolet mask using an extreme ultraviolet microscope** [9048-78]
T. Amano, T. Terasawa, H. Watanabe, EUVL Infrastructure Development Ctr., Inc. (Japan); M. Toyoda, Tohoku Univ. (Japan); T. Harada, T. Watanabe, H. Kinoshita, Univ. of Hyogo (Japan)

- 9048 29 **EUV resist dissolution optimization for CD uniformity and defect control in coat develop track process** [9048-80]
M. Harumoto, Dainippon Screen Manufacturing Co., Ltd. (Japan); H. Stokes, Y. Thouroude, Dainippon Screen Deutschland GmbH (Germany); O. Tamada, T. Miyagi, K. Kaneyama, Dainippon Screen Manufacturing Co., Ltd. (Japan); C. Pieczulewski, SOKUDO Co., Ltd. (Japan); M. Asai, Dainippon Screen Manufacturing Co., Ltd. (Japan)
- 9048 2A **Effect of defects on extreme ultraviolet pellicle** [9048-81]
I.-S. Kim, G.-J. Kim, Hanyang Univ. (Korea, Republic of); M. Yeung, Fastlitho Inc. (United States); E. Barouch, Boston Univ. (United States); M.-J. Kim, S.-S. Kim, SAMSUNG Electronics Co., Ltd. (Korea, Republic of); J.-W. Kim, H.-K. Oh, Hanyang Univ. (Korea, Republic of)
- 9048 2C **Evaluations of negative tone development resist and process for EUV lithography** [9048-83]
T. Takahashi, N. Fujitani, T. Itani, EUVL Infrastructure Development Ctr., Inc. (Japan)
- 9048 2D **Aerial image of mesh supported extreme ultraviolet pellicle** [9048-84]
K. Ko, G.-J. Kim, Hanyang Univ. (Korea, Republic of); M. Yeung, Fastlitho Inc. (United States); E. Barouch, Boston Univ. (United States); M.-J. Kim, S.-S. Kim, SAMSUNG Electronics Co., Ltd. (Korea, Republic of); H.-K. Oh, Hanyang Univ. (Korea, Republic of)
- 9048 2E **Super-flat wafer chucks: from simulation and testing to a complete 300mm wafer chuck with low wafer deformation between pins** [9048-85]
R. Müller, K. Afanasiev, M. Ziemann, V. Schmidt, Berliner Glas KGaA Herbert Kubatz GmbH & Co. (Germany)
- 9048 2F **Designing extreme-ultraviolet lithographic objective for 11 nm node** [9048-86]
Z. Cao, Y. Li, F. Liu, Beijing Institute of Technology (China)
- 9048 2G **EUV resist simulation based on process parameters of pattern formation reaction** [9048-87]
N. Sugie, T. Itani, EUVL Infrastructure Development Ctr., Inc. (Japan); T. Kozawa, Osaka Univ. (Japan)
- 9048 2H **OBPL for the best solution to resist outgassing and out-of-band issues in EUVL toward 1Xnm hp** [9048-88]
N. Fujitani, R. Sakamoto, T. Endo, H. Yaguchi, R. Onishi, Nissan Chemical Industries, Ltd. (Japan)
- 9048 2I **Temporal and spatial dynamics of a laser-produced plasma through a multiple Langmuir probe detector** [9048-89]
N. Gambino, M. Brandstätter, B. Rollinger, R. S. Abhari, ETH Zürich (Switzerland)
- 9048 2K **Clean and stable LPP light source for HVM inspection applications** [9048-91]
B. Rollinger, N. Gambino, A. Z. Giovannini, L. S. Bozinova, F. Alickaj, K. Hertig, R. S. Abhari, ETH Zürich (Switzerland); F. Abreau, Adlyte Ltd. (Switzerland)
- 9048 2M **Optimization of image-based aberration metrology for EUV lithography** [9048-93]
Z. Levinson, G. Fenger, A. Burbine, A. R. Schepis, B. W. Smith, Rochester Institute of Technology (United States)
- 9048 2N **Study of angular effects for optical systems into the EUV** [9048-94]
A. Burbine, Z. Levinson, A. Schepis, B. W. Smith, Rochester Institute of Technology (United States)

- 9048 2Q **Analysis of phase defect effect on contact hole pattern using a programmed phase defect in EUVL mask** [9048-97]
Y. Kim, T. Terasawa, T. Amano, EUVL Infrastructure Development Ctr., Inc. (Japan); S. Oh, Y. Hyun, SK Hynix Semiconductor Inc. (Korea, Republic of); H. Watanabe, EUVL Infrastructure Development Ctr., Inc. (Japan)
- 9048 2R **The factors affecting improvement sensitivity, CDU, and resolution in EUV resist** [9048-98]
J. Han, H. S. Lim, J. H. Kim, S. Choi, J. B. Shin, C. W. Bae, I. Y. Yoo, B. H. Shin, E. K. Lee, H. S. Joo, D. C. Seo, Korea Kumho Petrochemical Co., Ltd. (Korea, Republic of); J. S. Chun, SEMATECH Inc. (United States) and SUNY College of Nanoscale Science and Engineering (United States)
- 9048 2S **193nm inspection of extreme ultraviolet mask absorber defect** [9048-99]
G.-J. Kim, I.-S. Kim, Hanyang Univ. (Korea, Republic of); M. Yeung, Fastlitho Inc. (United States); C.-M. Lim, SK Hynix Semiconductor Inc. (Korea, Republic of); H.-K. Oh, Hanyang Univ. (Korea, Republic of)
- 9048 2V **Aerial image deformation caused by various defects of EUV pellicles** [9048-102]
S.-G. Lee, Hanyang Univ. (Korea, Republic of); M. Yeung, Fastlitho Inc. (United States); E. Barouch, Boston Univ. (United States); M.-J. Kim, S.-S. Kim, SAMSUNG Electronics Co., Ltd. (Korea, Republic of); H.-K. Oh, Hanyang Univ. (Korea, Republic of)
- 9048 2W **Correlation study on resist outgassing between EUV and e-beam irradiation** [9048-103]
Y. Kikuchi, K. Katayama, I. Takagi, N. Sugie, T. Takahashi, E. Shiobara, H. Tanaka, S. Inoue, EUVL Infrastructure Development Ctr., Inc. (Japan); T. Watanabe, T. Harada, H. Kinoshita, Univ. of Hyogo (Japan)
- 9048 2X **Predicting LER PSD caused by mask roughness using a mathematical model** [9048-104]
R. A. Claus, A. R. Neureuther, L. Waller, Univ. of California, Berkeley (United States); P. P. Naulleau, Lawrence Berkeley National Lab. (United States)
- 9048 2Z **Evaluation of EUV resist performance below 20nm CD using helium ion lithography** [9048-107]
D. Maas, E. van Veldhoven, TNO (Netherlands); A. van Langen-Suurling, P. F. A. Alkemade, Delft Univ. of Technology (Netherlands); S. Wuister, R. Hoefnagels, C. Verspaget, J. Meessen, T. Fliervoet, ASML Netherlands B.V. (Netherlands)
- 9048 31 **TNO reticle handling test platform** [9048-109]
W. E. Crowcombe, C. L. Hollemans, E. C. Fritz, J. C. J. van der Donck, N. B. Koster, TNO (Netherlands)
- 9048 34 **Stochastic and systematic patterning failure mechanisms for contact-holes in EUV lithography: Part 2** [9048-112]
A. Vaglio Pret, KLA-Tencor/ ICOS Belgium (Belgium) and IMEC (Belgium); P. De Bisschop, IMEC (Belgium); M. D. Smith, J. J. Biafore, KLA-Tencor (United States)
- 9048 35 **Laser produced plasma light source development for HVM** [9048-113]
I. V. Fomenkov, D. C. Brandt, N. R. Farrar, B. La Fontaine, D. W. Myers, D. J. Brown, A. I. Ershov, N. R. Böwering, D. J. Riggs, R. J. Rafac, S. De Dea, M. Purvis, Cymer LLC (United States); R. Peeters, H. Meiling, N. Harned, D. Smith, R. Kazinczi, A. Pirati, ASML Netherlands B.V. (Netherlands)

- 9048 37 **Limitations of resist-based characterization of EUV mask surface roughness** [9048-115]
S. Bhattarai, A. R. Neureuther, Univ. of California, Berkeley (United States) and Lawrence Berkeley National Lab. (United States); P. P. Naulleau, Lawrence Berkeley National Lab. (United States)
- 9048 38 **Clear sub-resolution assist features for EUV** [9048-116]
M. Burkhardt, IBM Research (United States); G. McIntyre, IBM Corp. (United States); R. Schlieff, L. Sun, GLOBALFOUNDRIES Inc. (United States)
- 9048 39 **Ptychographic wavefront sensor for high-NA EUV inspection and exposure tools** [9048-117]
A. Wojdyla, R. Miyakawa, P. Naulleau, Lawrence Berkeley National Lab. (United States)
- 9048 3A **AIS wavefront sensor: a robust optical test of exposure tools using localized wavefront curvature** [9048-118]
R. Miyakawa, Lawrence Berkeley National Lab. (United States); X. Zhou, SEMATECH Inc. (United States); M. Goldstein, SEMATECH Inc. (United States) and Intel Corp. (United States); D. Ashworth, K. Cummings, Y.-J. Fan, SEMATECH Inc. (United States); Y. Shroff, Intel Corp. (United States); G. Denbeaux, Y. Kandel, SUNY College of Nanoscale Science and Engineering (United States); P. Naulleau, Lawrence Berkeley National Lab. (United States)
- 9048 3B **High speed EUV using post processing and self-aligned double patterning as a speed enhancement technique** [9048-119]
J. Wandell, GLOBALFOUNDRIES Inc. (United States); A. deVilliers, L. Huli, TEL Technology Ctr., America, LLC (United States); S. Biesemans, Tokyo Electron Europe Ltd. (United Kingdom); K. Nafus, Tokyo Electron Kyushu Ltd. (Japan); M. Carcasi, Tokyo Electron America, Inc. (United States); J. Smith, D. Hetzer, TEL Technology Ctr., America, LLC (United States); C. Higgins, GLOBALFOUNDRIES Inc. (United States); V. Rastogi, TEL Technology Ctr., America, LLC (United States); E. Verduijn, GLOBALFOUNDRIES Inc. (United States)
- 9048 3C **Development of an EUVL collector with infrared radiation suppression** [9048-120]
M. Kriese, Y. Platonov, B. Ehlers, L. Jiang, J. Rodriguez, Rigaku Innovative Technologies, Inc. (United States); U. Mueller, J. Daniel, S. Khatri, A. Magruder, L-3 Communications Tinsley Labs. Inc. (United States); S. Grantham, C. Tarrio, T. Lucatorto, National Institute of Standards and Technology (United States)
- 9048 3D **Deconstructing contact hole CD printing variability in EUV lithography** [9048-121]
D. Civay, T. Wallow, N. Doganaksoy, GLOBALFOUNDRIES Inc. (United States); E. Verduijn, GLOBALFOUNDRIES Inc. (Belgium); G. Schmid, P. Mangat, GLOBALFOUNDRIES Inc. (United States)
- 9048 3E **Fast rigorous model for mask spectrum simulation and analysis of mask shadowing effects in EUV lithography** [9048-123]
X. Liu, X. Wang, S. Li, G. Yan, Shanghai Institute of Optics and Fine Mechanics (China); A. Erdmann, Fraunhofer Institute for Integrated Systems and Device Technology (IISB) (Germany)
- 9048 3F **At-wavelength observation of phase defect using focused lensless microscope** [9048-124]
T. Harada, Y. Tanaka, Univ. of Hyogo (Japan); T. Amano, Y. Usui, EUVL Infrastructure Development Ctr., Inc. (Japan); T. Watanabe, H. Kinoshita, Univ. of Hyogo (Japan)
- 9048 3H **Characterization of high-resolution HfSOx inorganic resists** [9048-126]
R. P. Oleksak, G. S. Herman, Oregon State Univ. (United States)

- 9048 3L **Investigating printability of native defects on EUV mask blanks through simulations and experiments** [9048-130]
M. Upadhyaya, SUNY College of Nanoscale Science and Engineering (United States);
V. Jindal, SEMATECH Inc. (United States); H. Herbol, SUNY College of Nanoscale Science
and Engineering (United States); I.-Y. Jang, H. J. Kwon, J. Harris-Jones, SEMATECH Inc.
(United States); G. Denbeaux, SUNY College of Nanoscale Science and Engineering
(United States)
- 9048 3M **Evaluating vacuum components for particle performance for EUV lithography** [9048-131]
Y. Khopkar, G. Denbeaux, SUNY College of Nanoscale Science and Engineering (United
States); V. Jindal, SEMATECH Inc. (United States)

Author Index

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 (Korea, Republic of)
Masaki Yoshioka, XTREME technologies GmbH (Germany)

Session Chairs

- 1 Invited Session
Jos P. Benschop, ASML Netherlands B.V. (Netherlands)
Shinji Okazaki, Gigaphoton Inc. (Japan)
- 2 New EUV Resist Materials: Joint Session with Conferences 9048 and 9051
Robert L. Brainard, SUNY College of Nanoscale Science and Engineering (United States)
James W. Thackeray, Dow Electronic Materials (United States)
- 3 Stochastics and EUV Process Improvements: Joint Session with Conferences 9048 and 9051
Roel Gronheid, IMEC (Belgium)
Uzodinma Okoroanyanwu, Consultant (Germany)
- 4 EUV Source
Sang Hun Lee, Intel Corporation (United States)
Michael J. Lercel, SEMATECH Inc. (United States)
- 5 EUV Mask I
Frank Goodwin, SEMATECH Inc. (United States)
Hidehiro Watanabe, EUVL Infrastructure Development Center, Inc. (Japan)
- 6 EUV Mask II
Pawitter J. Mangat, GLOBALFOUNDRIES Inc. (United States)
Guojing Zhang, Intel Corporation (United States)

- 7 EUV Integration
Patrick P. Naulleau, Lawrence Berkeley National Laboratory
(United States)
Anthony Yen, TSMC Taiwan (Taiwan)
- 8 EUV Mask Metrology
Ted Liang, Intel Corporation (United States)
Jan Hendrik Peters, Carl Zeiss SMS GmbH (Germany)
- 9 Metrology Sources and Modeling
Michael Goldstein, SEMATECH Inc. (United States)
Jorge J. Rocca, Colorado State University (United States)
- 10 EUV Resist Outgas Testing
Soichi Inoue, EUVL Infrastructure Development Center, Inc. (Japan)
Kurt G. Ronse, IMEC (Belgium)
- 11 EUV Resist I
Thomas I. Wallow, ASML US, Inc. (United States)
Christopher S. Ngai, Applied Materials, Inc. (United States)
- 12 Exposure Tools and Extendibility
Eric M. Panning, Intel Corporation (United States)
Stefan Wurm, SEMATECH Inc. (United States) and
GLOBALFOUNDRIES Inc. (United States)
- 13 EUV Manufacturing
Matthew E. Colburn, IBM Corporation (United States)
Seong-Sue Kim, SAMSUNG Electronics Company, Ltd.
(Korea, Republic of)

Introduction

The chairs of the Extreme Ultraviolet (EUV) Lithography V conference would like to thank the program committee, the session chairs, the presenters and the attendees for a successful 2014 meeting at SPIE Advanced Lithography in San Jose, California. Conference oral talks were up year over year with excellent worldwide representation. Peak session attendance at invited and joint sessions topped 600. Key topics included EUV scanner performance and EUV pellicle program progress, source scaling challenges including in-situ collector cleaning, mask metrology results from both the SHARP actinic microscope at LBNL and the Zeiss EUV AIMSTM tool, performance improvements in novel resist formulations, and improvement in on-product overlay, edge placement error (EPE) understanding, and EUV cost of ownership modeling.

The EUV conference received 135 abstract submissions in 2014, an increase of ~14% over the previous year. The receipt of a record number of abstract this year, 68 of which were accepted for oral presentation and 67 for presentation in the poster session, is evidence of the increasing interest in EUV lithography technology as it gets closer to HVM introduction. The 2014 SPIE Advanced Lithography Symposium preregistration totaled 2,360. This was up ~6% from 2013's count of 2230. The average attendance at the EUV conference was 332 per session and the peak attendance in the invited sessions was 629. Both stats were up from the 2013 numbers of 258 and 620 respectively.

Attendance by session is presented in Table 1.

Session	Count
Invited 1	629
Joint with PM (Resist)	614
Source	245
Mask 1	202
Mask 2	214
Integration	230
Mask Metrology	212
Metrology Sources	201
Outgassing	331
Resists	353
Tools & Extendibility	369
Manufacturing	388

Submissions by region for 2014 and 2013 are shown in Figure 2.

2014 Conference Highlights

Scanners

ASML has delivered two NXE:3300B EUV scanners to customers, while installation has started on three additional systems. Six more NXE:3300Bs are currently in various stages of integration, and ASML has already begun work on its next generation EUV scanner, the NXE:3350¹. The first projection optics (POB) for an NXE:3350 scanner has an rms wave front error (wfe) of ~0.2 nm—significantly lower than the wfe in a typical NXE:3300B POB. Some champion printing results obtained with a NXE:3300B scanner using 90°-dipole illumination are 16 nm lines and spaced at 10% exposure latitude (EL) and 100 nm depth of focus (DOF) and 24 nm regular 1:1 contact holes at 18% EL and >120 nm DOF and a full wafer CDU of 1.2 nm (3 σ). The best full-wafer dedicated chuck overlay for an NXE:3300B scanner is ~1.4 nm (3 σ).

In-use reticle defectivity continues to remain challenging. The fall-on particle rate (at 92 nm sensitivity) in a 20 hour test of 7 NXE platform systems varied from 0.00 to 0.04 particles per reticle pass—a number that will need to be improved by ~100X for high volume manufacturing (HVM). ASML presented excellent progress in their pellicle development program². Photographs of two free-standing polysilicon membranes 106 mm × 139 mm in size were shown. One was 70 nm thick and had an EUV transmission of ~82%, and the other was 57 nm thick and had an estimated transmission of ~84%. The target for EUV pellicle transmission is <90% in a single pass and ~81% in a double pass.

Sources

ASML reported 30 W of EUV power from a production LPP source resulting in 100% die yield (percentage of simulated dies meeting the 0.5% dose repro spec).¹

ASML/Cymer reported achieving 70 W of power at intermediate focus for six minutes in a low-rep-rate master-oscillator-power-amplifier (MOPA) LPP source at their factory in San Diego³. ASML's current productivity target is 70 wafers per hour (wph) in 2014 and 125 wph in 2015. TSMC reported that the no-master-oscillator (NOMO) LPP source in its NXE:3100 scanner typically provides ~ 10W at intermediate focus (IF) which would correspond to a scanner productivity of ~8 wph using ASML's ATP (acceptance test protocol)⁴. Researchers from the Univ. of Illinois at Urbana-Champaign described an in-situ hydrogen-based collector cleaning process with a Sn removal rate of 1.1 nm/minute at an RF power of 300 W and that no sputtering or other damage to the collector optic was observed⁵.

Zeiss/Helmholtz Zentrum Berlin gave an interesting invited paper on accelerator-based EUV sources⁶. A design for a free-electron-laser (FEL) oscillator capable of > 1.0 kW of output power at 13.5 nm wavelength was described. The power level in an FEL oscillator will be limited by the maximum intracavity power that the cavity mirrors can handle. According to the presenter, the x-ray FEL source in Hamburg, Germany routinely operates with a reliability exceeding 90%. Even though the estimated cost of a FEL EUV source is expected to be >100M€, such a source should be able to supply power to more than one EUV scanner.

Metrology

Five years ago it was not possible to properly inspect EUV masks. Since then, SEMATECH's AIT tool and more recently SHARP actinic microscope have demonstrated excellent progress/results⁷. At this conference Zeiss reported that first light had been achieved in their EUV AIMSTTM tool and showed some very high quality actinic images of 2D mask patterns⁸. This achievement appears to have removed the last remaining technical risk from Zeiss's EUV AIMSTTM tool program and the first delivery of tools that can review the printability of 30-45 nm defects (7-11 nm at the wafer) is now expected to take place in 2015.

TSMC reported that defect-free masks can be fabricated using pattern shift defect mitigation given EUV mask blanks with < 20 defects at 25 nm SEVD size and accurate blank defect maps⁴. In other words, actinic pattern mask inspection tools may not be needed.

Materials

Continued progress on chemically amplified resist platforms was reported. JSR showed images of 16.7 nm lines and spaces printed at 46.5 mJ/cm² dose⁹ and Fujifilm showed images of 14 nm hp features printed at 30.8 mJ/cm² dose¹⁰. Continued progress using novel organic/inorganic resist chemistries was reported as well. Inpria showed images of 22 nm lines and spaces with an LWR of only 2.0 nm (3 σ) in a 20 nm thick film of their Generation 2 patternable hardmask material that can be developed with 2-heptanone¹¹. A group at Cornell University showed images of ~20 nm lines and spaces¹² in ZrO₂ – based material with an LER of only 5-7 nm using an EUV dose of only 1.4 – 1.6 mJ/cm² and in HfO₂ –based material with an LER of only 3-5 nm using an EUV dose of only 2.5 mJ/cm².

Manufacturing

ASML reported that the current best NXE to NXT on-product overlay, using an optimized 18 parameter/field correction recipe, is 5.3 nm (3σ) in x and 5.4 nm (3σ) in y¹³. The on-product overlay target for the 7 nm technology node is ~ 3.0 nm (3σ).

Intel reported that as the basic CD and overlay performance of scanners have improved the relative magnitude of other contributions to the total edge placement error (EPE) have grown. The author presented a detailed model developed with Mike Hanna of ASML that identifies the root cause of machine to machine overlay errors and suggests ways to help minimize them¹⁴.

IMEC presented cost of ownership estimates when using EUV litho at the 10 and 7 nm nodes. The author claimed that 193i side-wall-assisted-quadruple-patterning (SAQP) lithography will increase the cost of patterning back-end-of-line (BEOL) levels by ~16% when going from the 10 nm to the 7 nm technology node. And that the introduction of EUV lithography single exposure patterning will balance the cost of 193i SAQP when the EUV scanner throughput is above 55 wph¹⁵.

2015 Conference Call For Papers

In 2014 the installation and ramp up of the first group of production EUVL scanners will be completed. In 2015 EUV lithography technology development will require higher power sources for full loop process development and optimization. Several critical technical challenges remain, i.e., fielding EUV sources with the power and reliability required for productive exposure tool throughput, mitigating all remaining printable mask blank defects, and developing manufacturing ready resists. Looking longer term, many important questions with respect to the extendibility of the technology to 7 nm and beyond remain unanswered. Chief among these are the roles of advanced resolution enhancement techniques, double-patterning EUVL, higher NA EUV imaging systems, new source technologies like FEL, and resist stochastic effects. Technical and scientific papers advancing the state of the art in EUV Lithography are solicited.

Obert R. Wood II
Eric M. Panning

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